NPN Silicon Epitaxial Planar Transistor for switching and AF amplifier applications.

These transistors are subdivided into three groups Q, R and S according to their DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T $_a = 25^{\circ}$ C)

	Symbol	Value		Unit
		ST 2SC828	ST 2SC828A	
Collector Base Voltage	V _{CBO}	30	45	V
Collector Emitter Voltage	V _{CEO}	25	45	V
Emitter Base Voltage	V _{EBO}	7		V
Peak Collector Current	I _{CM}	100		mA
Collector Current	Ic	50		mA
Power Dissipation	P _{tot}	400		mW
Junction Temperature	T _j	150		°C
Storage Temperature Range	Ts	-55 to +150		°С

G S P FORM A IS AVAILABLE



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ST 2SC828 / 828A

Characteristics at T_{amb}=25 °C

			Symbol	Min.	Тур.	Max.	Unit
DC Current Gain							
at I _C =2mA, V _{CE} =5V							
	Current Gain Group	Q	h_{FE}	130	-	280	-
		R	h_{FE}	180	-	360	-
		S	h_{FE}	260	-	520	-
Collector Base Breakdown Voltage							
at I _C =10μA	ST 2SC828		$V_{(BR)CBO}$	30	-	-	V
	ST 2SC828	Α	$V_{(BR)CBO}$	45	-	-	V
Collector Emitter Breakdown Voltage							
at I _C =2mA	ST 2SC828		$V_{(BR)CEO}$	25	-	-	V
	ST 2SC828	Α	$V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdown Voltage							
at I _E =10μA			$V_{(BR)EBO}$	7	-	-	V
Collector Saturation Vo	oltage						
at I _C =50mA, I _B =5mA			$V_{CE(sat)}$	-	0.14	-	V
Base Emitter Voltage							
at I _C =10mA, V _{CE} =5V			V_{BE}	-	-	0.8	V
Gain Bandwidth Produ	ct						
at I _C =-2mA, V _{CE} =10V			f_T		220		MHz
Noise Figure							
at V _{CE} =5V,I _E =0.2mA,			NF	-	6	-	dB
$R_G=2k\Omega, f=1kHz$							

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